

BRCS300P016ZJ

Rev.A Sep.-2022

DFN 2×2B-6L P MOS

P-Channel Enhancement Mode Field Effect Transistor in a DFN 2×2B-6L Plastic Package.

$V_{DS} (V) = -16V$ $I_D = -11A$

$R_{DS(ON)} @ -4.5V \leq 32m\Omega$

。 HF Product.

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

/ Absolute Maximum Ratings($T_c=25$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-16	V
Gate-Source Voltage	V_{GSS}	± 8	V
Continuous Drain Current	I_D	-11	A
Pulsed Drain Current	I_{DM}	-44	A
Avalanche Current	I_{AS}	21	A
Avalanche energy $L=0.5mH$	E_{AS}	308	mJ
Power Dissipation for Single Operation	P_D	15.5	W
Maximum Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 150	$^{\circ}C$
Thermal Resistance-Junction to Ambient	$R_{JC} \quad t \quad 10s$	8	$^{\circ}C/W$

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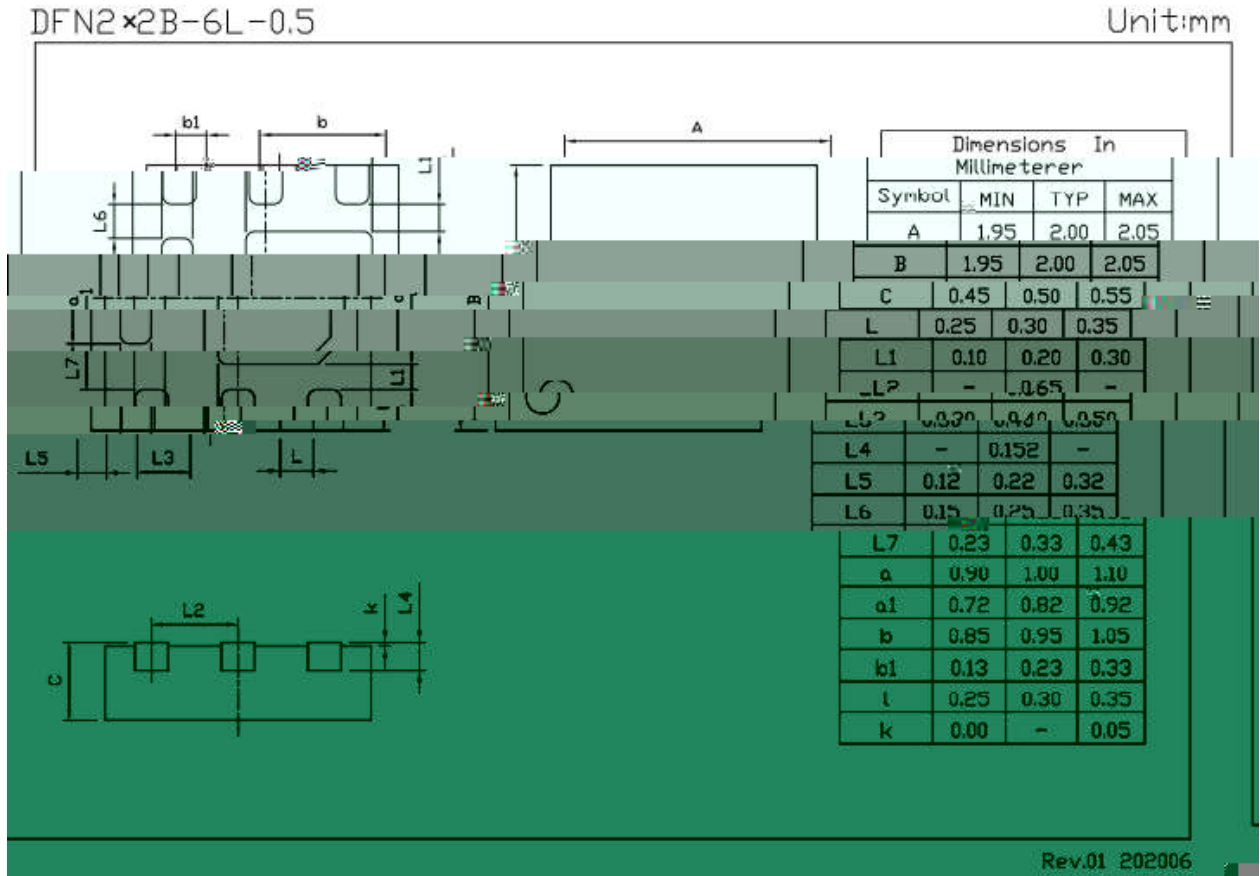
DATA SHEET

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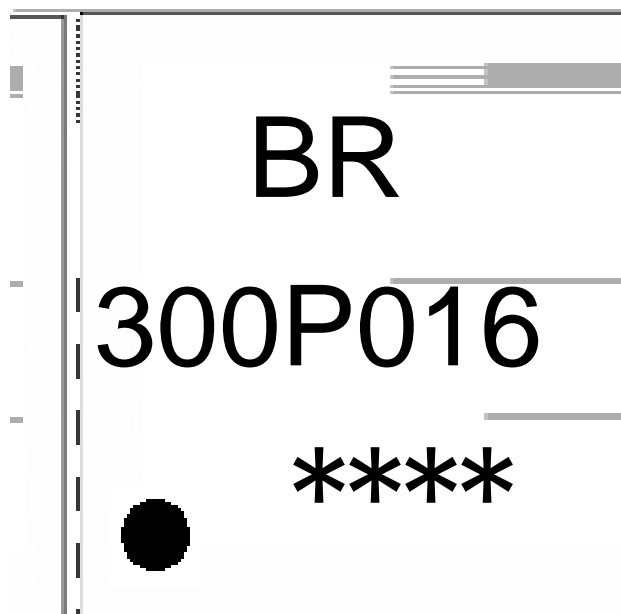
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/ Package Dimensions

DFN2×2B-6L-0.5 外形尺寸图



/ Marking Instructions



BR

300P016

Note:

BR: Company Code

300P016: Product Type

*****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note: